

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-713	SERIAL NO. 08/886,388	
<div style="position: relative; width: 100px; height: 100px; margin: 0 auto;"> <div style="position: absolute; top: 0; left: 0; right: 0; bottom: 0; border: 2px solid black; border-radius: 50%; text-align: center; line-height: 100px; font-size: 24px; font-weight: bold;">O I P E</div> <div style="position: absolute; top: 10%; left: 10%; font-size: 12px;">APR 09 1999</div> <div style="position: absolute; top: 50%; left: 50%; transform: translate(-50%, -50%); font-size: 10px;">LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</div> </div>				APPLICANT Gurtej S. Sandhu et al.		
				FILING DATE Filed herewith		GROUP 2811
U.S. PATENT DOCUMENTS						
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
SWC	AA	4,558,509	12/1985	Tiwari		
	AB	4,568,565	2/1986	Gupta et al.		
	AC	5,023,683	6/91	Yamada		
	AD	5,053,351	10/91	Fazan et al.		
	AE	5,071,781	12/91	Seo et al.		
	AF	5,130,172	7/92	Hicks et al.		
	AG	5,139,825	8/92	Gordon et al.		
	AH	5,168,073	12/92	Gonzalez et al.		
	AI	5,216,267	6/93	Jin et al.		
	AJ	5,223,729	6/93	Kudoh et al.		
SWC	AK	5,290,726	3/94	Kim		
FOREIGN PATENT DOCUMENTS						
	Document Number	Date	Country	Class	Subclass	Translation Yes No
	AL					
	AN					
	AO					
	AP					
OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)						
SWC	AR		Conrad, J.R. et al., "Ion Beam Assisted Coating And Surface Modification With Plasma Source Ion Implantation", J. Vac. Sci. Technol. A 8 (4), Jul/Aug, 1990, 3146-3151			
SWC	AS		Temmler, D., "Multilayer Vertical Stacked Capacitors (MVSTC) for 64 Mbit and 256 mBit DRAMs", Article, Institute of Semiconductor Physics, Germany, no date, 2 pgs.			
SWC	AT		Niemer, B., et al., "Organometallic Chemical Vapor Deposition of Tungsten Metal, and Suppression of Carbon Incorporation by Codeposition of Platinum", Article, University of California, Los Angeles, CA, Dept. of Chemistry and Biochemistry, published 8/4/92, 3 pgs.			
EXAMINER CRANE			DATE CONSIDERED 6/18/99			
<p><small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small></p>						

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*Examiner Initial	Document Number	Date	Title	Class	Subclass		
S W C	AA	5,300,321	4/94	Nakano et al.			
	AB	5,320,878	6/94	Maya			
	AC	5,330,614	7/94	Ahn			
	AD	5,403,620	4/95	Kuesz et al.			
	AE	5,508,218	4/96	Jun			
	AF	5,006,481	04/91	Chan et al.	437	52	
	AG	5,021,357	06/91	Taguchi et al.	437	52	
	AH	5,061,651	10/91	Ino	437	52	
	AI	5,116,776	05/92	Chan et al.	437	52	
	AJ	5,135,883	08/92	Bae et al.	437	52	
S W C	AK	5,164,337	11/92	Ogawa et al.	437	228	
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AL						
	AM						
	AN						
	AO						
OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)							
S W C	AR		T. Morihara et al., "Disk-Shaped Stacked Capacitor Cell for 256 Mb Dynamic Random-Access Memory", Aug. 19, 1994,				
			Jpn. J. Appl. Phys. Vol. 33 (1994), Pt. 1, No. 8, pp. 14-19				
S W C	AS		S. Woo et al., "Selective Etching Technology of in-situ P Doped Poly-Si (SEDOP) for High Density DRAM Capacitors",				
			1994 Symposium on VLSI Technology Digest of Technical Papers, pp. 25-26				
S W C	AT		H. Watanabe et al., "Stacked Capacitor Cells for High-density dynamic RAMs", IEDM 1988, pp. 600-603				
EXAMINER <div style="font-size: 1.5em; font-weight: bold;">CRANE</div>				DATE CONSIDERED <div style="font-size: 1.5em; font-weight: bold;">6/18/99</div>			
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SWC	AA 5,170,233	12/92	Liu et al.	257	308		
SWC	AB 5,622,882	04/97	Yee	438	210		
SWC	AC 5,631,184	05/97	Ikemasu et al.	438	397		
	AD						
	AE						
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	AJ						
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	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
SWC	AR		Inoue, S., et al., "A Spread Stacked Capacitor (SCC) Cell for 64MBIT DRAMs", IEEE 1989, pp. 31-34 (2.3.1 - 2.3.4).				
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